

**SONY**

**CXA1276K**

**8-bit 500 MSPS Flash A/D Converter**

*Preliminary*

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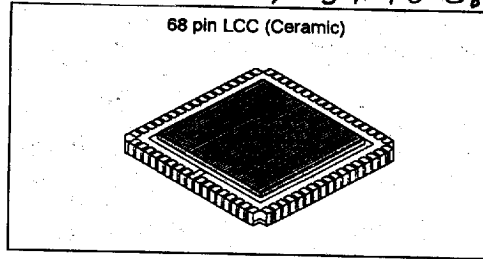
*T-51-10-08*

**Description**

The CXA1276K is a 8-bit ultrahigh-speed flash A/D converter IC capable of Digitizing analog signals at a maximum rate of 500 MSPS. The digital I/O levels of these A/D converters are compatible with the ECL 100K/10KH/10K.

**Features**

- Differential linearity error:  $\pm 1/2$  LSB or less
- Integral linearity error:  $\pm 1/2$  LSB or less
- Built-in integral linearity compensation circuit
- Ultrahigh-speed operation with maximum conversion rate of 500 MSPS (Min.)
- Low input capacitance: 16pF (Typ.)
- Wide analog input bandwidth: 250MHz (Typ. for full-scale input)
- Single power supply: -5.2V
- Low power consumption: 2.2W (Typ.)
- Low error rate
- Good temperature characteristics
- Capable of driving 50  $\Omega$  loads



**Structure**

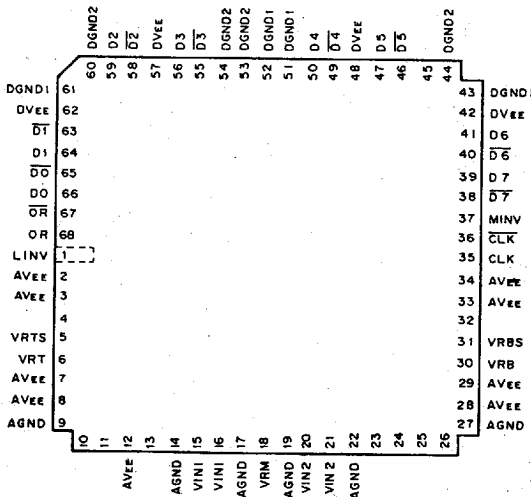
Bipolar silicon monolithic IC

**Applications**

- Digital oscilloscopes
- Radar
- Other apparatus requiring ultrahigh-speed A/D conversion

**Pin Configuration**

Pins without name are NC pins (not connected internally).



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**Absolute Maximum Ratings (Ta=25°C)**

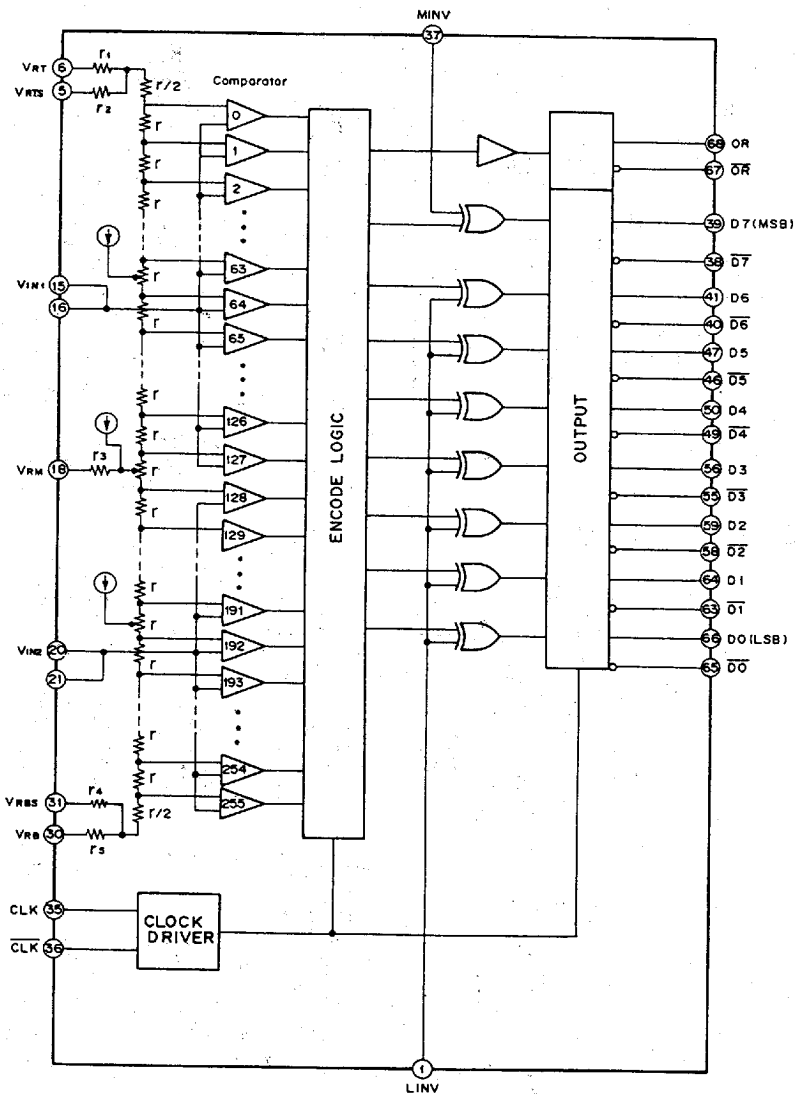
• Supply voltage	AV <sub>EE</sub> , DV <sub>EE</sub>	-7 to +0.5	V
• Analog input voltage	V <sub>IN</sub>	-2.7 to +0.5	V
• Reference input voltage	V <sub>RT</sub> , V <sub>RB</sub> , V <sub>RM</sub>	AV <sub>EE</sub> to +0.5	V
	V <sub>RT</sub> -V <sub>RB</sub>	2.5	V
• Digital input voltage	MINV, LINV	-4 to +0.5	V
	CLK, $\overline{\text{CLK}}$	DV <sub>EE</sub> to +0.5	V
	CLK - $\overline{\text{CLK}}$	2.7	V
• V <sub>RM</sub> pin input current	I <sub>VRM</sub>	-3 to +3	mA
• Digital output current	ID <sub>0</sub> to ID <sub>7</sub> , IOR, $\overline{\text{ID}}_0$ to $\overline{\text{ID}}_7$ , $\overline{\text{IOR}}$	-30 to 0	mA
• Operating temperature	T <sub>a</sub>	-25 to +100	°C
	T <sub>c</sub>	-25 to +125	°C
• Storage temperature	T <sub>stg</sub>	-65 to +150	°C

**Operating Conditions**

		Min.	Typ.	Max.	Unit
• Supply voltage	AV <sub>EE</sub> , DV <sub>EE</sub>	-5.5	-5.2	-4.95	V
	AV <sub>EE</sub> -DV <sub>EE</sub>	-0.05	0	0.05	V
	AGND-DGND	-0.05	0	0.05	V
• Reference input voltage	V <sub>RT</sub>	-0.1	0	0.1	V
	V <sub>RB</sub>	-2.2	-2.0	-1.8	V
• Analog input voltage	V <sub>IN</sub>	V <sub>RB</sub>		V <sub>RT</sub>	

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Block Diagram



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Pin Description

Pin No.	Symbol	I/O	Standard voltage level	Equivalent circuit	Description
1	LINV	I	ECL		Polarity selection for LSBs. (Refer to the table of Input voltage vs. Digital output) L level is maintained with left open.
37	MINV	I	ECL		Polarity selection for MSB (Refer to the table of Input voltage vs. Digital output) L level is maintained with left open.
6	VRT	I	0V		Analog reference voltage (Top) (0V Typ.)
5	VRTS	O	0V		Reference voltage sense (Top)
18	VRM	I	$V_{RB}/2$		Reference voltage mid-point It can be used for linearity compensation.
31	VRBS	O	-2V		Reference voltage sense (Bottom)
30	VRB	I	-2V		Analog reference voltage (Bottom)
15 16	VIN1	I	VRTS to VRBS		Analog input All of the pins must be wired externally.
20 21	VIN2				
35	CLK	I	ECL		CLK input
36	CLK	I	ECL		Complementary CLK input $V_{BS}$ (-1.3V) is maintained with left open.

Pin No.	Symbol	I/O	Standard voltage level	Equivalent circuit	Description	
39 38	D <sub>7</sub> D <sub>7</sub>	O	ECL		MSB and complementary MSB output	
41 40	D <sub>6</sub> D <sub>6</sub>	O	ECL		<p>D<sub>1</sub> to D<sub>6</sub>: Output D<sub>1</sub>-bar to D<sub>6</sub>-bar: Complementary output</p>	
47 46	D <sub>5</sub> D <sub>5</sub>	O	ECL			
50 49	D <sub>4</sub> D <sub>4</sub>	O	ECL			
56 55	D <sub>3</sub> D <sub>3</sub>	O	ECL			
59 58	D <sub>2</sub> D <sub>2</sub>	O	ECL			
64 63	D <sub>1</sub> D <sub>1</sub>	O	ECL			
66 65	D <sub>0</sub> D <sub>0</sub>	O	ECL			
68 67	OR OR	O	ECL			
2, 3, 7, 8, 12, 28, 29, 33, 34	AV <sub>EE</sub> *		-5.2V			
9, 14, 17, 19, 22, 27	AGND *		0V	Analog ground		
42, 48, 57, 62	DVEE *		-5.2V	Digital supply Internally connected with AV <sub>EE</sub> (resistance : 4 to 6 Ω).		
43, 51, 52, 61	DGND1 *		0V	Digital ground		
44, 53, 54, 60	DGND2 *		0V	Digital ground for output drive		
4, 10, 11, 13, 23, 24, 25, 26, 32	NC		—	No connect pins It is recommended to wire these pins to AGND.		
45	NC		—	No connect pins It is recommended to wire these pins to DGND.		

\* All of these pins must be wired to the respective external circuit.

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## Electrical Characteristics

(A<sub>VEE</sub>=D<sub>VEE</sub>=-5.2V, V<sub>RT</sub>, V<sub>RTS</sub>=0V, V<sub>RB</sub>, V<sub>RS</sub>=-2V)

Item	Symbol	Condition	Test level *1	Min.	Typ.	Max.	Unit
Resolution					8		bits
DC characteristics							
Integral linearity error	E <sub>IL</sub>	F <sub>c</sub> =500MHz	II		± 0.3	± 0.5	LSB
Differential linearity error	E <sub>DL</sub>	F <sub>c</sub> =500MHz	II		± 0.3	± 0.5	LSB
Analog input							
Analog input capacitance	C <sub>IN</sub>	V <sub>IN</sub> =-1V+0.07V <sub>rms</sub>	IV		16		pF
Analog input resistance	R <sub>IN</sub>		IV		100		kΩ
Input bias current	I <sub>IN</sub>	V <sub>IN</sub> =-1V	IV			620	μA
Reference inputs							
Reference resistance	R <sub>REF</sub>		II		110		Ω
Frequency characteristic of reference resistance	F <sub>REF</sub>		IV		10		MHz
Residual resistance *2	r1		IV		0.6		Ω
	r2		IV		500		Ω
	r3		IV		2.0		Ω
	r4		IV		500		Ω
	r5		IV		0.6		Ω
Digital inputs							
Logic H level	V <sub>IH</sub>		IV	-1.165			V
Logic L level	V <sub>IL</sub>		IV			-1.475	V
Logic H current	I <sub>IH</sub>	Input connected to GND	IV			100	μA
Logic L current	I <sub>IL</sub>	Input connected to -2V	IV	-100			μA
Input capacitance			IV		7		pF
Switching characteristics							
Maximum conversion rate	F <sub>c</sub>		II	400			MSPS
Aperture jitter	T <sub>aj</sub>		IV		5		ps
Sampling delay	T <sub>ds</sub>		IV		1.0		ns
Output delay	T <sub>do</sub>		IV		2.0		ns
H pulse width of clock	T <sub>pw1</sub>		IV	1.2			ns
L pulse width of clock	T <sub>pw0</sub>		IV	1.2			ns
Digital outputs							
Logic H level	V <sub>OH</sub>	R <sub>L</sub> =50 Ω	II	-1.025			V
Logic L level	V <sub>OL</sub>	R <sub>L</sub> =50 Ω	II			-1.620	V
Output rising time	T <sub>r</sub>	R <sub>L</sub> =50 Ω	IV		1.0		ns
Output falling time	T <sub>f</sub>	R <sub>L</sub> =50 Ω	IV		1.0		ns

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Item	Symbol	Condition	Test level *1	Min.	Typ.	Max.	Unit
Dynamic characteristics							
Full scale input bandwidth		V <sub>IN</sub> =2V <sub>p-p</sub>	IV		300		MHz
Small-signal input bandwidth		V <sub>IN</sub> =0.6V <sub>p-p</sub>	IV		500		MHz
S/N ratio		{ Input=1kHz, FS Clock=500MHz	IV		46		dB
		{ Input=99.999MHz, FS Clock=500MHz	IV		40		dB
Error rate		{ Input=1kHz, FS Error>16LSB Clock=99.999MHz	IV			10 <sup>-12</sup>	TPS *3
		{ Input=62.499MHz, FS Error>16LSB Clock=500MHz	II			10 <sup>-9</sup>	TPS *3
Differential gain error	DG	} NTSC 40 IRE mod. ramp, Fc=500MSPS	IV			1.0	%
Differential phase error	DP		IV			0.5	deg
Overrange recovery time			IV			1.0	ns
Power supply							
Analog supply current	I <sub>EEA</sub>		II		320		mA
Digital supply current	I <sub>EED</sub>		II		100		mA
Power consumption *4	P <sub>d</sub>		II		2200		mW

\*1 Test levels

- I..... All-quantity test over full operating temperature range (T<sub>c</sub>=-25 to +125°C)
- II..... All-quantity test at T<sub>c</sub>=+25°C
- III..... Sampling test only
- IV..... Design specifications
- V..... Typical values only

\*2 See Block Diagram

\*3 TPS: times per sample

\*4 
$$P_d = I_{EEA} \cdot A_{VEE} + I_{EED} \cdot D_{VEE} + \frac{(V_{RT} - V_{RB})^2}{R_{REF}}$$

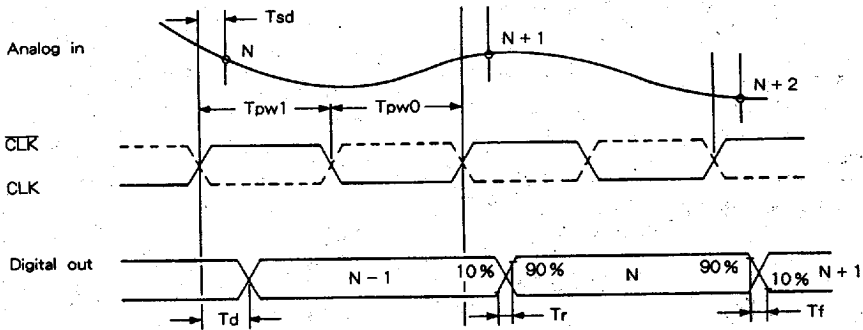
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Input Voltage vs. Digital Output

V <sub>IN</sub> *	Step	MINV 1 LINV 1		0 1			1 0			0 0		
		OR	D7 D0	OR	D7 D0	OR	D7 D0	OR	D0 D7			
0V	0	0	000.....00	0	100.....00	0	011.....11	0	111.....11			
		1	000.....00	1	100.....00	1	011.....11	1	111.....11			
		1	000.....01	1	100.....01	1	011.....10	1	111.....10			
			⋮		⋮		⋮		⋮			
-1V	127 128	1	011.....11	1	111.....11	1	000.....00	1	100.....00			
		1	100.....00	1	000.....00	1	111.....11	1	011.....11			
			⋮		⋮		⋮		⋮			
-2V	254 255	1	111.....10	1	011.....10	1	100.....01	1	000.....01			
		1	111.....11	1	011.....11	1	100.....00	1	000.....00			
		1	111.....11	1	011.....11	1	100.....00	1	000.....00			

\* V<sub>RT</sub>=V<sub>RTS</sub>=0V, V<sub>RM</sub>=-1V or Open, V<sub>RB</sub>=V<sub>RBS</sub>=-2V

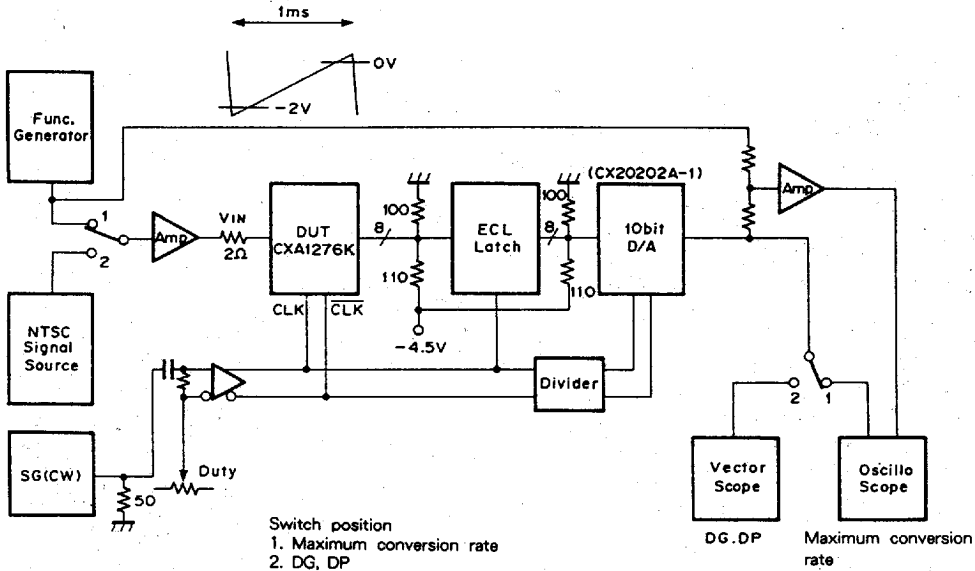
Timing Diagram



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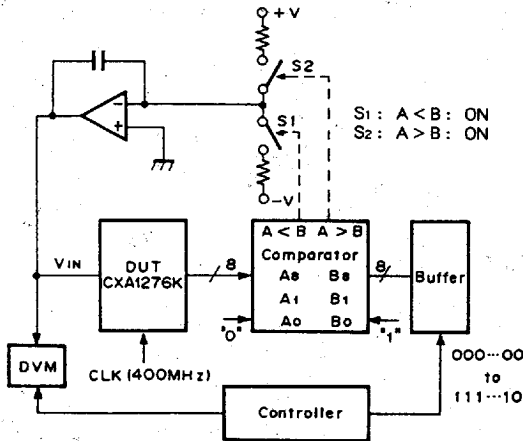
**Electrical Characteristics Test Circuit**

- Maximum conversion rate test circuit
- Differential gain error test circuit
- Differential phase error test circuit



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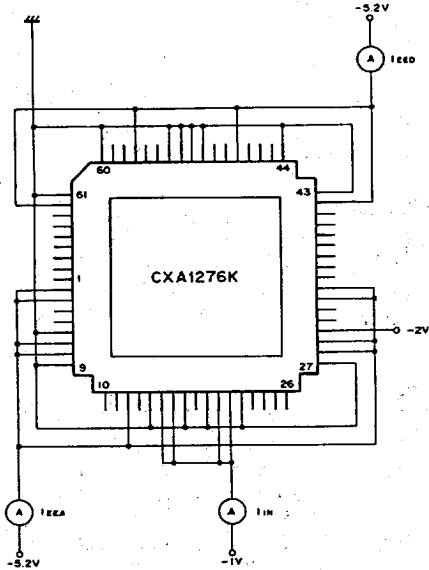
**Integral linearity error test circuit**  
**Differential linearity error test circuit**



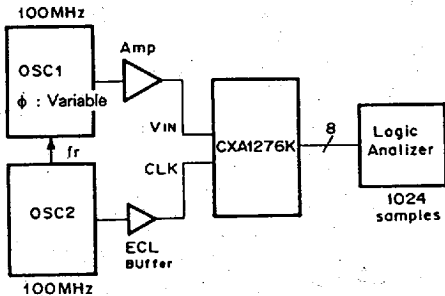
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**Power Supply Current Test Circuit**

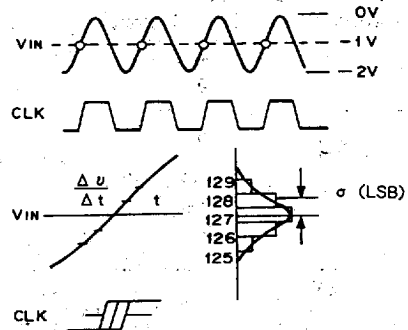
**Analog Input bias current test circuit**



**Sampling delay test circuit**  
**Aperture jitter test circuit**



**Aperture jitter test method**



Aperture jitter

Aperture jitter is defined as follows:

$$T_{aj} = \sigma / \frac{\Delta v}{\Delta t} = \sigma / \left( \frac{256}{2} \times 2 \pi f \right)$$

Where  $\sigma$  (unit: LSB) is the deviation of the output codes when the input frequency is exactly the same as the clock and is sampled at the largest slew rate point.

